Bruce W Wessels

List of Publications by Year
in descending order

251 papers	9,049 citations	53660 45 h-index	49773 87 g-index
253 all docs	253 docs citations	253 times ranked	8628 citing authors

#	Article	IF	Citations
1	Photoluminescence spectroscopy of excitonic emission in CsPbCl3 perovskite single crystals. Journal of Luminescence, 2022, 243, 118661.	1.5	11
2	Defect levels in CsPbCl3 single crystals determined by thermally stimulated current spectroscopy. Journal of Applied Physics, 2022, 132, .	1.1	6
3	CsPbBr3 perovskite detectors with 1.4% energy resolution for high-energy Î³-rays. Nature Photonics, 2021, 15, 36-42.	15.6	210
4	Demonstration of Energy-Resolved Î³-Ray Detection at Room Temperature by the CsPbCl₃ Perovskite Semiconductor. Journal of the American Chemical Society, 2021, 143, 2068-2077.	6.6	62
5	Inorganic Halide Perovskitoid TlPbI₃ for Ionizing Radiation Detection. Advanced Functional Materials, 2021, 31, 2006635.	7.8	16
6	Excitons in CsPbBr₃ Halide Perovskite. Journal of Physical Chemistry Letters, 2021, 12, 9301-9307.	2.1	8
7	Direct thermal neutron detection by the 2D semiconductor 6LiInP2Se6. Nature, 2020, 577, 346-349.	13.7	59
8	Perovskites with a Twist: Strong In¹⁺ Off-Centering in the Mixed-Valent CsInX₃ (X = Cl, Br). Chemistry of Materials, 2019, 31, 9554-9566.	3.2	22
9	Monte Carlo simulation of transport properties in wide gap Hg3Se2I2. Semiconductor Science and Technology, 2019, 34, 115003.	1.0	1
10	Purification and Improved Nuclear Radiation Detection of Tl₆SI₄ Semiconductor. Crystal Growth and Design, 2019, 19, 4738-4744.	1.4	4
11	Controlling the Vapor Transport Crystal Growth of Hg₃Se₂I₂ Hard Radiation Detector Using Organic Polymer. Crystal Growth and Design, 2019, 19, 2074-2080.	1.4	7
12	From 0D Cs₃Bi₂I₉ to 2D Cs₃Bi₂I₆Cl₃: Dimensional Expansion Induces a Direct Band Gap but Enhances Electronâ€“Phonon Coupling. Chemistry of Materials, 2019, 31, 2644-2650.	3.2	111
13	Carrier recombination mechanism in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>CsPbB</mml:mi><mml:msub><mml:mi mathvariant="normal">r</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math> revealed by time-resolved photoluminescence spectroscopy. Physical Review B, 2019, 100, .	1.1	14
14	Noise sources and their limitations on the performance of compound semiconductor hard radiation detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2019, 916, 133-140.	0.7	4
15	Perovskite CsPbBr3 single crystal detector for alpha-particle spectroscopy. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2019, 922, 217-221.	0.7	83
16	High spectral resolution of gamma-rays at room temperature by perovskite CsPbBr3 single crystals. Nature Communications, 2018, 9, 1609.	5.8	381
17	An Effective Purification Process for the Nuclear Radiation Detector Tl₆SeI₄. Crystal Growth and Design, 2018, 18, 3484-3493.	1.4	9
18	Cu₂I₂Se₆: A Metalâ€“Inorganic Framework Wide-Bandgap Semiconductor for Photon Detection at Room Temperature. Journal of the American Chemical Society, 2018, 140, 1894-1899.	6.6	19

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19	Role of Stoichiometry in the Growth of Large Pb₂P₂Se₆ Crystals for Nuclear Radiation Detection. ACS Photonics, 2018, 5, 566-573.	3.2	15
20	Dynamic Disorder, Band Gap Widening, and Persistent Near-IR Photoluminescence up to At Least 523 K in ASnI₃ Perovskites (A = Cs⁺, CH₃NH₃⁺) Tj ETQq0 0 rgBT /Overlock 26353-26361.	1.5	26
21	Deep Level and Nearâ€Bandâ€Edge Recombination in Semiconducting Antiperovskite Hg₃Se₂I₂ Single Crystals. Advanced Optical Materials, 2018, 6, 1800328.	3.6	2
22	Resolving the Energy of Î³-Ray Photons with MAPbI₃ Single Crystals. ACS Photonics, 2018, 5, 4132-4138.	3.2	100
23	Î±-Particle Detection and Charge Transport Characteristics in the A₃M₂I₉ Defect Perovskites (A = Cs, Rb; M = Bi, Sb). ACS Photonics, 2018, 5, 3748-3762.	3.2	88
24	Defect Antiperovskite Compounds Hg₃Q₂I₂ (Q = S, Se, and Te) for Room-Temperature Hard Radiation Detection. Journal of the American Chemical Society, 2017, 139, 7939-7951.	6.6	45
25	Strong Electronâ€“Phonon Coupling and Self-Trapped Excitons in the Defect Halide Perovskites A₃M₂I₉ (A = Cs, Rb; M = Bi, Sb). Chemistry of Materials, 2017, 29, 4129-4145.	3.2	509
26	TlSn₂I₅, a Robust Halide Antiperovskite Semiconductor for Î³-Ray Detection at Room Temperature. ACS Photonics, 2017, 4, 1805-1813.	3.2	33
27	Charge Transport and Observation of Persistent Photoconductivity in Tl₆SeI₄ Single Crystals. Journal of Physical Chemistry Letters, 2017, 8, 1538-1544.	2.1	15
28	TlSbS₂: a Semiconductor for Hard Radiation Detection. ACS Photonics, 2017, 4, 2891-2898.	3.2	11
29	Electronic defects in the halide antiperovskite semiconductor <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Hg</mml:mi><mml:mn>3</mml:mn></mml:msub><mml:msub><mml:mi mathvariant="normal">I</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math>. Physical Review B, 2017, 96, .	1.1	3
30	Improved Crystal Growth of Tl₆SeI₄ for Î³-Ray Detection Material by Oxide Impurity Removal. Crystal Growth and Design, 2017, 17, 6096-6104.	1.4	6
31	$chi ^{(2)}$ Modulator With 40-GHz Modulation Utilizing BaTiO3 Photonic Crystal Waveguides. IEEE Journal of Quantum Electronics, 2017, 53, 1-10.	1.0	26
32	Cascaded spintronic logic with low-dimensional carbon. Nature Communications, 2017, 8, 15635.	5.8	39
33	Charge Transport Mechanisms in a Pb₂P₂Se₆ Semiconductor. ACS Photonics, 2016, 3, 1877-1887.	3.2	6
34	Refined Synthesis and Crystal Growth of Pb₂P₂Se₆ for Hard Radiation Detectors. Crystal Growth and Design, 2016, 16, 5100-5109.	1.4	12
35	Photoluminescence fatigue and inhomogeneous line broadening in semi-insulating Tl₆SeI₄single crystals. Semiconductor Science and Technology, 2016, 31, 065009.	1.0	16
36	Integrated BaTiO3 modulator with 8 dB extinction at 50 GHz and 25 km reach. , 2016, , .		2

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37	An Unusual Crystal Growth Method of the Chalcohalide Semiconductor, Î²-Hg₃S₂Cl₂: A New Candidate for Hard Radiation Detection. Crystal Growth and Design, 2016, 16, 2678-2684.	1.4	16
38	High-field magnetic circular dichroism in ferromagnetic InMnSb and InMnAs: Spin-orbit-split hole bands and<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>g</mml:mi></mml:math>factors. Physical Review B, 2015, 92, .	1.1	8
39	Direct observation of wide band-gap luminescence in the single-crystal perovskite semiconductors<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>CsPbB</mml:mi><mml:msub><mml:mi mathvariant="normal">r</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>and<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>CsPbC</mml:mi><mml:msub><mml:mi mathvariant="normal">l</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>. Physical Review B, 2015, 92, .	1.1	250
40	Mn doped InSb studied at the atomic scale by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2015, 107, .	1.5	4
41	Bilayer avalanche spin-diode logic. AIP Advances, 2015, 5, 117102.	0.6	8
42	Hard Radiation Detection from the Selenophosphate Pb₂P₂Se₆. Advanced Functional Materials, 2015, 25, 4874-4881.	7.8	33
43	Emitter-Coupled Spin-Transistor Logic: Cascaded Spintronic Computing Beyond 10 GHz. IEEE Journal on Emerging and Selected Topics in Circuits and Systems, 2015, 5, 17-27.	2.7	11
44	Characterization of deep level defects in Tl6I4S single crystals by photo-induced current transient spectroscopy. Journal Physics D: Applied Physics, 2015, 48, 075303.	1.3	2
45	Charge Transport in Magnetic Semiconductor p-n Heterojunctions. IEEE Transactions on Electron Devices, 2015, 62, 2470-2474.	1.6	5
46	Magnetism and Mn Clustering in (In,Mn)Sb Magnetic Semiconductors. ACS Applied Materials & Interfaces, 2015, 7, 24159-24167.	4.0	18
47	Optical investigation of defects in semi-insulating<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi mathvariant="normal">Tl</mml:mi><mml:mn>6</mml:mn></mml:msub></mml:math><mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi mathvariant="normal">I</mml:mi><mml:mn>4</mml:mn></mml:msub><mml:mtext>S</mml:mtext></mml:math>single crystals. Physical Review B, 2014, 90, .	1.1	7
48	High-performance computing based on spin-diode logic. Proceedings of SPIE, 2014, , .	0.8	1
49	Emitter-coupled spin-transistor logic. Journal of Parallel and Distributed Computing, 2014, 74, 2461-2469.	2.7	8
50	Investigation of Semi-Insulating Cs₂Hg₆S₇ and Cs₂Hg_{6-x}Cd_xS₇ Alloy for Hard Radiation Detection. Crystal Growth and Design, 2014, 14, 5949-5956.	1.4	11
51	Crystal Growth of Tl₄CdI₆: A Wide Band Gap Semiconductor for Hard Radiation Detection. Crystal Growth and Design, 2014, 14, 2401-2410.	1.4	35
52	Photo-induced current transient spectroscopy of single crystal Tl₆I₄Se. Semiconductor Science and Technology, 2014, 29, 115002.	1.0	6
53	Cs₂M^{II}M^{IV}₃Q₈ (Q = S, Se, Te): An Extensive Family of Layered Semiconductors with Diverse Band Gaps. Chemistry of Materials, 2013, 25, 3344-3356.	3.2	75
54	Photoconductivity in Tl₆SI₄: A Novel Semiconductor for Hard Radiation Detection. Chemistry of Materials, 2013, 25, 2868-2877.	3.2	45

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55	Transient photocurrent measurements in alkali chalcogenide ternary compound semiconductors. Semiconductor Science and Technology, 2013, 28, 015022.	1.0	7
56	Crystal Growth of the Perovskite Semiconductor CsPbBr₃: A New Material for High-Energy Radiation Detection. Crystal Growth and Design, 2013, 13, 2722-2727.	1.4	1,234
57	CsCdInQ₃ (Q = Se, Te): New Photoconductive Compounds As Potential Materials for Hard Radiation Detection. Chemistry of Materials, 2013, 25, 2089-2099.	3.2	50
58	Photonic Crystal Waveguide Electro-Optic Modulator With a Wide Bandwidth. Journal of Lightwave Technology, 2013, 31, 1601-1607.	2.7	29
59	Photoconductivity in the Chalcohalide Semiconductor, SbSeI: a New Candidate for Hard Radiation Detection. Inorganic Chemistry, 2013, 52, 7045-7050.	1.9	55
60	MAGNETORESISTANCE OF NARROW GAP MAGNETIC SEMICONDUCTOR HETEROJUNCTIONS. Spin, 2013, 03, 1340011.	0.6	0
61	Cyclotron resonance in ferromagnetic InMnAs and InMnSb. Physical Review B, 2013, 88, .	1.1	15
62	Magnetoresistance in InMnAs/InAs heterojunctions and its dependence on alloy composition and temperature. Applied Physics Letters, 2013, 103, .	1.5	4
63	InMnAs magnetoresistive spin-diode logic. , 2012, , .		5
64	Photoluminescent properties of semiconducting Tl₆I₄Se. Semiconductor Science and Technology, 2012, 27, 015016.	1.0	5
65	Emitter-coupled spin-transistor logic. , 2012, , .		4
66	Investigation of defect levels in Cs2Hg6S7 single crystals by photoconductivity and photoluminescence spectroscopies. Journal of Applied Physics, 2012, 112, 063702.	1.1	14
67	Structural and magnetic properties of epitaxial In1â€“xMnxSb semiconductor alloys with xâ€‰›â€‰0.08. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 032801.	0.6	5
68	CsHgInS₃: a New Quaternary Semiconductor for Î³-ray Detection. Chemistry of Materials, 2012, 24, 4434-4441.	3.2	56
69	Characterization of InMnSb epitaxial films for spintronics. Journal of Physics: Conference Series, 2012, 371, 012032.	0.3	4
70	Mercury and antimony chalcohalide semiconductors as new candidates for radiation detection applications at room temperature. Proceedings of SPIE, 2012, , .	0.8	8
71	Formation of native defects in the Î³-ray detector material Cs2Hg6S7. Applied Physics Letters, 2012, 101, .	1.5	11
72	A Spin-Diode Logic Family. IEEE Nanotechnology Magazine, 2012, 11, 1026-1032.	1.1	28

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73	Ferromagnetic InMnSb multi-phase films study by aberration-corrected (scanning) transmission electron microscopy. Journal of Applied Physics, 2012, 111, 07C311.	1.1	32
74	Crystal Growth and Characterization of the X-ray and Î³-ray Detector Material Cs₂Hg₆S₇. Crystal Growth and Design, 2012, 12, 3250-3256.	1.4	42
75	Time-resolved differential transmission in MOVPE-grown ferromagnetic InMnAs. Physical Review B, 2012, 85, .	1.1	13
76	Spin-dependent magnetotransport in a p-InMnSb/n-InSb magnetic semiconductor heterojunction. Applied Physics Letters, 2011, 98, 193506.	1.5	20
77	Dimensionally reduced heavy atom semiconductors as candidate materials for Î³-ray detection: the case of Cs₂Hg₆S₇. Materials Research Society Symposia Proceedings, 2011, 1341, 1.	0.1	3
78	Thallium Chalcogenide-Based Wide-Band-Gap Semiconductors: TlGaSe₂ for Radiation Detectors. Chemistry of Materials, 2011, 23, 3120-3128.	3.2	87
79	Thallous chalcogenide (Tl6I4Se) for radiation detection at X-ray and Î³-ray energies. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2011, 659, 333-335.	0.7	19
80	Thallium Chalcohalides for X-ray and Î³-ray Detection. Journal of the American Chemical Society, 2011, 133, 10030-10033.	6.6	105
81	Dimensional Reduction: A Design Tool for New Radiation Detection Materials. Advanced Materials, 2011, 23, 4163-4167.	11.1	185
82	Alkali Metal Chalcogenides for Radiation Detection. Materials Research Society Symposia Proceedings, 2011, 1341, 1.	0.1	3
83	Cyclotron resonance in InMnAs and InMnSb ferromagnetic films. Journal of Physics: Conference Series, 2011, 334, 012056.	0.3	2
84	Local electronic and magnetic structure of mixed ferrite multilayer materials. Physical Review B, 2010, 81, .	1.1	9
85	Strain-driven spin reorientation in magnetite/barium titanate heterostructures. Applied Physics Letters, 2010, 96, .	1.5	32
86	Using the infrared magnetorefractive effect to compare the magnetoresistance in (100) and (111) oriented Fe3O4 films. Journal of Applied Physics, 2010, 107, 09B102.	1.1	9
87	High-temperature ferromagnetism in epitaxial (In,Mn)Sb films. Physical Review B, 2010, 81, .	1.1	25
88	Magnetoamplification in a Bipolar Magnetic Junction Transistor. Physical Review Letters, 2010, 105, 117202.	2.9	39
89	Magnetotransport properties of InMnSb magnetic semiconductor thin films. Physical Review B, 2010, 82, .	1.1	54
90	Ferroelectric Thin Film Microcavities and their Optical Resonant Properties. Materials Research Society Symposia Proceedings, 2009, 1182, 24.	0.1	1

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91	Polarization reversal and backswitching dynamics in epitaxial BaTiO3 thin films. Journal of Applied Physics, 2009, 106, 054113.	1.1	18
92	Giant magnetoresistance of magnetic semiconductor heterojunctions. Physical Review B, 2009, 79, .	1.1	29
93	Electronic structure of substitutional Mn in epitaxial In0.965Mn0.035Sb film. Applied Physics Letters, 2009, 95, 201905.	1.5	7
94	Ferromagnetic semiconductors and the role of disorder. New Journal of Physics, 2008, 10, 055008.	1.2	30
95	Highly efficient broadband second harmonic generation using polydomain epitaxial barium titanate thin film waveguides. Applied Physics Letters, 2008, 92, .	1.5	16
96	Magnetocapacitance effect in InMnAsâˆ•InAs p-n heterojunctions. Journal of Vacuum Science & Technology B, 2008, 26, 1526.	1.3	3
97	Interfacial structure and chemistry of epitaxial CoFe2O4 thin films on SrTiO3 and MgO substrates. Applied Physics Letters, 2008, 93, 181901.	1.5	41
98	Dynamic response of polydomain ferroelectric barium titanate epitaxial thin films and its field dependence. Journal of Applied Physics, 2008, 104, 064115.	1.1	8
99	Epitaxial growth and strain relaxation of BaTiO[sub 3] thin films on SrTiO[sub 3] buffered (001) Si by molecular beam epitaxy. Journal of Vacuum Science & Technology B, 2007, 25, 1053.	1.3	40
100	Phase stability of heteroepitaxial polydomain BaTiO3 thin films. Journal of Materials Research, 2007, 22, 1384-1389.	1.2	5
101	Bragg Reflector Waveguide and Electro-Optic Modulator Based on Barium Titanate Epitaxial Thin Films. Materials Research Society Symposia Proceedings, 2007, 1014, 1.	0.1	0
102	Simulation and Fabrication of Two Dimensional Nonlinear Photonic Crystals using Barium Titanate Thin Films. Materials Research Society Symposia Proceedings, 2007, 1014, 1.	0.1	4
103	Dependence of magnetic circular dichroism on doping and temperature in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mi mathvariant="normal">In</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^’</mml:mo><mml:mi>x</mml:mi></mml:mrow></ mathvariant="normal">Mn</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:mi mathvariant="normal">As</mml:mi></mml:mrow></mml:math>epitaxial films. Physical Review B, 2007, 76, .	1.1	14
104	Ferroelectric Epitaxial Thin Films for Integrated Optics. Annual Review of Materials Research, 2007, 37, 659-679.	4.3	149
105	High-field magnetoresistance in p-(In,Mn)Asâˆ•n-InAs heterojunctions. Applied Physics Letters, 2006, 88, 072105.	1.5	26
106	InMnAs/InAs Heterojunctions for High-Field Magnetic Sensors. , 2006, , .		0
107	Epitaxial growth and strain relaxation of MgO thin films on Si grown by molecular beam epitaxy. Journal of Vacuum Science & Technology B, 2006, 24, 2586.	1.3	28
108	Evidence of room temperature sp-d exchange in InMnAs epitaxial films. Applied Physics Letters, 2006, 89, 102505.	1.5	10

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109	Measurement of Minority Carrier Diffusion Lengths in Semiconductor Nanowires. , 2006, , .		1
110	Low temperature deposition of epitaxial BaTiO[sub 3] films in a rotating disk vertical MOCVD reactor. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1674.	1.6	15
111	Local environment of ferromagnetically ordered Mn in epitaxial InMnAs. Applied Physics Letters, 2005, 86, 072505.	1.5	16
112	Optical investigation of electronic states of Mn4+ ions in p-type GaN. Applied Physics Letters, 2005, 86, 042505.	1.5	30
113	BaTiO_3 thin-film waveguide modulator with a low voltageâ€“length product at near-infrared wavelengths of 098 and 155 Âµm. Optics Letters, 2005, 30, 254.	1.7	40
114	Investigation of composition fluctuations in GaN:Mg using optical transmission spectroscopy, near-field scanning optical microscopy, and scanning Kelvin probe microscopy. Journal of Applied Physics, 2005, 98, 023513.	1.1	13
115	Negative magnetoresistance in(In,Mn)Assemiconductors. Physical Review B, 2004, 70, .	1.1	35
116	Optical properties of Mn4+ ions in GaN:Mn codoped with Mg acceptors. Applied Physics Letters, 2004, 84, 5320-5322.	1.5	32
117	Three Dimensional Domain Structure in Epitaxial Barium Titanate Thin Films. Journal of Electroceramics, 2004, 13, 89-93.	0.8	13
118	Thin Film Ferroelectrics for Guided Wave Devices. Journal of Electroceramics, 2004, 13, 135-138.	0.8	9
119	Integration of MgO on Si(001) Using SrO and SrTiO3 Buffer Layers by Molecular Beam Epitaxy. Journal of Electroceramics, 2004, 13, 149-154.	0.8	6
120	Phonon-assisted deep level luminescence in heavily Mg-doped InGaN. Journal of Electronic Materials, 2004, 33, 431-435.	1.0	3
121	Local structure around Mn atoms in room-temperature ferromagnetic (In,Mn)As thin films probed by extended x-ray absorption fine structure. Applied Physics Letters, 2004, 84, 481-483.	1.5	45
122	Low-voltage, polarization-insensitive, electro-optic modulator based on a polydomain barium titanate thin film. Applied Physics Letters, 2004, 85, 4615-4617.	1.5	66
123	Electrooptic modulation up to 40 GHz in a barium titanate thin film waveguide modulator. Optics Express, 2004, 12, 5962.	1.7	85
124	Blue emission band in compensated GaN:Mg codoped with Si. Physical Review B, 2003, 68, .	1.1	30
125	Nanosecond-Scale Domain Dynamics in BaTiO 3 Probed by Time-Resolved X-Ray Diffraction. Ferroelectrics, 2003, 290, 115-124.	0.3	6
126	Dielectric properties of plasma-spray-deposited BaTiO3 and Ba0.68Sr0.32TiO3 thick films. Journal of Materials Research, 2003, 18, 1227-1231.	1.2	9

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127	Relative dielectric constant of epitaxial BaTiO3 thin films in the GHz frequency range. Applied Physics Letters, 2003, 83, 5274-5276.	1.5	46
128	Phase stability of epitaxial KTaxNb1â^'xO3 thin films deposited by metalorganic chemical vapor deposition. Journal of Materials Research, 2003, 18, 106-110.	1.2	16
129	Dynamic response of the dielectric and electro-optic properties of epitaxial ferroelectric thin films. Physical Review B, 2002, 65, .	1.1	23
130	Optical properties of the deep Mn acceptor in GaN:Mn. Applied Physics Letters, 2002, 80, 1731-1733.	1.5	152
131	Dielectric properties of epitaxial KNbO3 ferroelectric thin films. Journal of Materials Research, 2002, 17, 275-278.	1.2	22
132	Ferromagnetism in (In,Mn)As diluted magnetic semiconductor thin films grown by metalorganic vapor phase epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1582.	1.6	30
133	Deep Donor-Acceptor Pair Luminescence in Codoped GaN. Materials Research Society Symposia Proceedings, 2002, 743, L5.8.1.	0.1	1
134	Interfacial Layer Effects in Ba1-xSrxTiO3 Thick Films prepared by Plasma Spray. Materials Research Society Symposia Proceedings, 2002, 758, 271.	0.1	2
135	Diffuse Phase Transition in Epitaxial BaTiO3 Thin Films. Journal of Materials Research, 2002, 17, 669-674.	1.2	21
136	Fast time-resolved x-ray diffraction in BaTiO3 films subjected to a strong high-frequency electric field. Applied Physics Letters, 2002, 80, 3159-3161.	1.5	24
137	Electrical properties ofp-type GaN:Mg codoped with oxygen. Applied Physics Letters, 2001, 78, 222-224.	1.5	88
138	Comparative optical studies of p-type and unintentionally doped GaN: The influence of annealing. Applied Physics Letters, 2001, 78, 58-60.	1.5	13
139	Erbium-Doped Barium Titanate Thin FilmWaveguides For Integrated Optical Amplifiers. Materials Research Society Symposia Proceedings, 2001, 688, 1.	0.1	3
140	Erbium-Doped Barium Titanate Thin Film Waveguides For Integrated Optical Amplifiers. Materials Research Society Symposia Proceedings, 2001, 694, 1.	0.1	0
141	Dielectric Properties of Spray Deposited BaTiO₃ and Ba_{0.68}Sr_{0.32}TiO₃. Materials Research Society Symposia Proceedings, 2001, 698, 361.	0.1	2
142	Growth and characterization of OMVPE grown (In,Mn)As diluted magnetic semiconductor. Journal of Electronic Materials, 2001, 30, 1408-1411.	1.0	48
143	Metalorganic Molecular Beam Epitaxy of Magnesium Oxide on Silicon. Materials Research Society Symposia Proceedings, 2000, 619, 149.	0.1	7
144	Epitaxial Ferroelectric BaTiO₃ Thin Films for Microphotonic Applications. Materials Research Society Symposia Proceedings, 2000, 637, E1.9.1.	0.1	8

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145	Deep Level Formation in Undoped and Oxygen-Doped GaN. Materials Research Society Symposia Proceedings, 2000, 639, 11561.	0.1	0
146	Photoluminescence Studies of p-type GaN:Mg Co-doped with Oxygen. Materials Research Society Symposia Proceedings, 2000, 639, 6391.	0.1	2
147	MOCVD of Epitaxial BaTiO3 Films Using a Liquid Barium Precursor. Chemical Vapor Deposition, 2000, 6, 175-177.	1.4	32
148	Combinatorial Generation and Analysis of Nanometer- and Micrometer-Scale Silicon Features via â€œDip-Penâ€•Nanolithography and Wet Chemical Etching. Advanced Materials, 2000, 12, 1600-1603.	11.1	129
149	Electrical Properties of Oxygen Doped GaN Grown by Metalorganic Vapor Phase Epitaxy. MRS Internet Journal of Nitride Semiconductor Research, 2000, 5, 301-307.	1.0	14
150	Photoluminescence band near 2.9 eV in undoped GaN epitaxial layers. Journal of Applied Physics, 2000, 87, 3351-3354.	1.1	103
151	Optical Study of GaN Doped with Mn Grown by Metal Organic Vapor Phase Epitaxy. Materials Research Society Symposia Proceedings, 2000, 639, 371.	0.1	6
152	Investigation of the formation of the 2.8 eV luminescence band in p-type GaN:Mg. Applied Physics Letters, 2000, 76, 3011-3013.	1.5	108
153	Pressure dependence of the blue luminescence in Mg-doped GaN. Applied Physics Letters, 2000, 77, 2536-2538.	1.5	6
154	Combinatorial Generation and Analysis of Nanometer- and Micrometer-Scale Silicon Features via â€œDip-Penâ€•Nanolithography and Wet Chemical Etching. , 2000, 12, 1600.		2
155	Defect Luminescence in Heavily Mg Doped GaN. MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 968-973.	1.0	4
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